

General Description

The AO4440 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

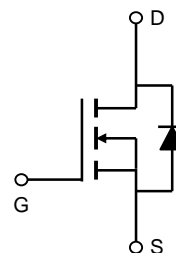
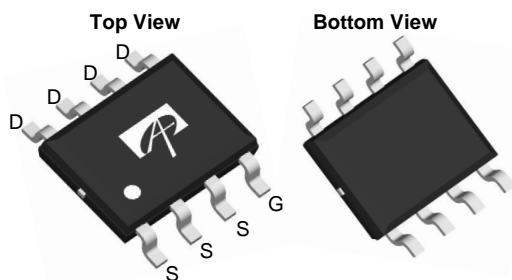
Product Summary

V_{DS} (V) = 60V
 I_D = 5A (V_{GS} = 10V)
 $R_{DS(ON)}$ < 55m Ω (V_{GS} = 10V)
 $R_{DS(ON)}$ < 75m Ω (V_{GS} = 4.5V)

100% UIS Tested
 100% Rg Tested



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|------------------------|------------|------------------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current ^A | $T_A=25^\circ\text{C}$ | 5 | A |
| | $T_A=70^\circ\text{C}$ | 4 | |
| Pulsed Drain Current ^B | I_{DM} | 20 | |
| Power Dissipation | $T_A=25^\circ\text{C}$ | 2.5 | W |
| | $T_A=70^\circ\text{C}$ | 1.6 | |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | | Symbol | Typ | Max | Units |
|--|---------------------|-----------------|-----|-----|--------------------|
| Maximum Junction-to-Ambient ^A | $t \leq 10\text{s}$ | $R_{\theta JA}$ | 38 | 50 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Ambient ^A | Steady-State | | 69 | 80 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Lead ^C | Steady-State | $R_{\theta JL}$ | 24 | 30 | $^\circ\text{C/W}$ |

N Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|---|-----|----------|--------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0V | 60 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =48V, V _{GS} =0V T _J =55°C | | | 1 5 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} = ±20V | | | 100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} I _D =250μA | 1 | 2.3 | 3 | V |
| I _{D(ON)} | On state drain current | V _{GS} =10V, V _{DS} =5V | 20 | | | A |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} =10V, I _D =5A T _J =125°C | | 42 75 | 55 | mΩ |
| | | V _{GS} =4.5V, I _D =4A | | 54 | 75 | |
| | | | | | | mΩ |
| g _{FS} | Forward Transconductance | V _{DS} =5V, I _D =5A | | 11 | | S |
| V _{SD} | Diode Forward Voltage | I _S =1A, V _{GS} =0V | | 0.78 | 1 | V |
| I _S | Maximum Body-Diode Continuous Current | | | | 4 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =30V, f=1MHz | | 450 | 540 | pF |
| C _{oss} | Output Capacitance | | | 60 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 25 | | pF |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, f=1MHz | | 1.65 | 2 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q _g (10V) | Total Gate Charge | V _{GS} =10V, V _{DS} =30V, I _D =5A | | 8.5 | 10.5 | nC |
| Q _g (4.5V) | Total Gate Charge | | | 4.3 | 5.5 | nC |
| Q _{gs} | Gate Source Charge | | | 1.6 | | nC |
| Q _{gd} | Gate Drain Charge | | | 2.2 | | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =10V, V _{DS} =30V, R _L =6Ω, R _{GEN} =3Ω | | 5.1 | 7 | ns |
| t _r | Turn-On Rise Time | | | 2.6 | 4 | ns |
| t _{D(off)} | Turn-Off DelayTime | | | 15.9 | 20 | ns |
| t _f | Turn-Off Fall Time | | | 2 | 3 | ns |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =5A, dI/dt=100A/μs | | 25.1 | 35 | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =5A, dI/dt=100A/μs | | 28.7 | | nC |

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating. Rev2: Nov. 2010

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CHANNEL

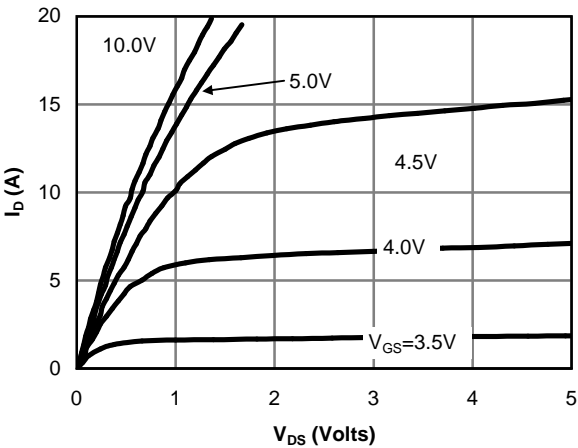


Fig 1: On-Region Characteristics

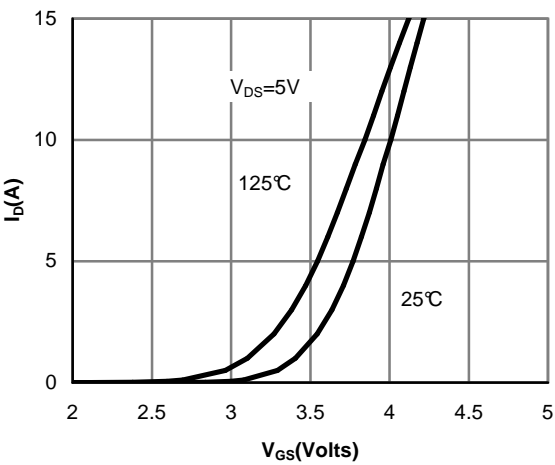


Figure 2: Transfer Characteristics

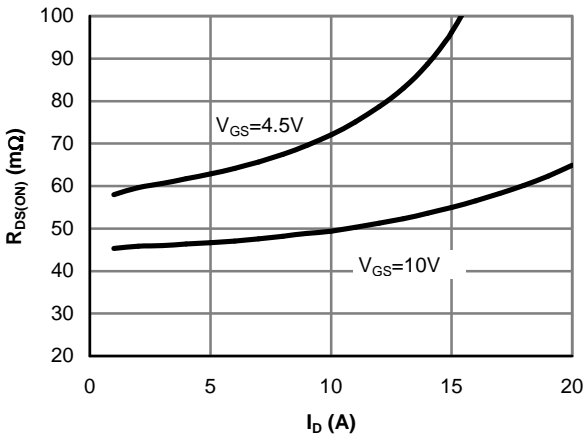


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

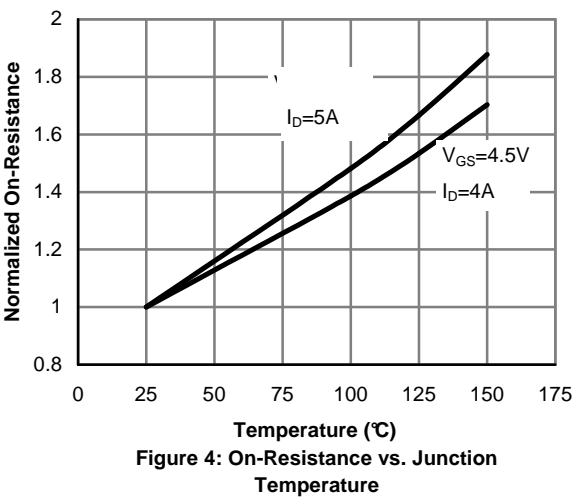


Figure 4: On-Resistance vs. Junction Temperature

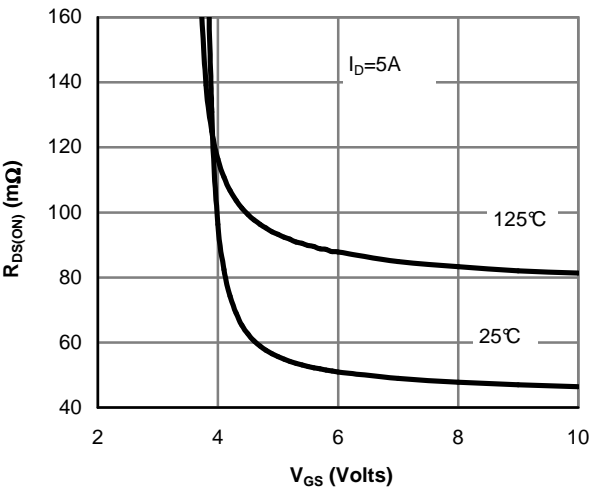


Figure 5: On-Resistance vs. Gate-Source Voltage

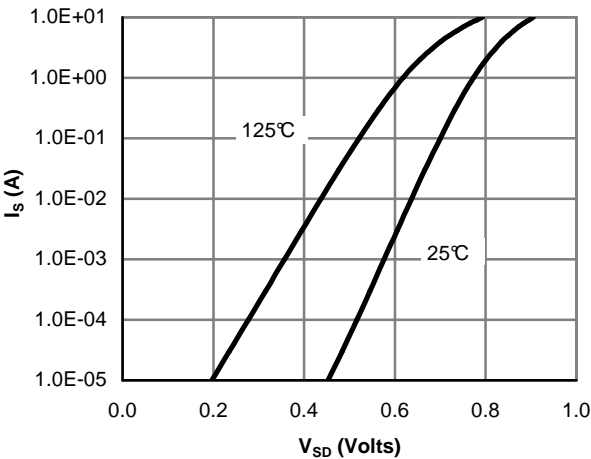


Figure 6: Body-Diode Characteristics

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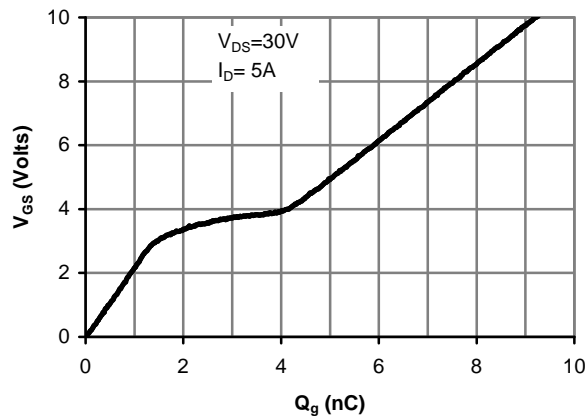


Figure 7: Gate-Charge Characteristics

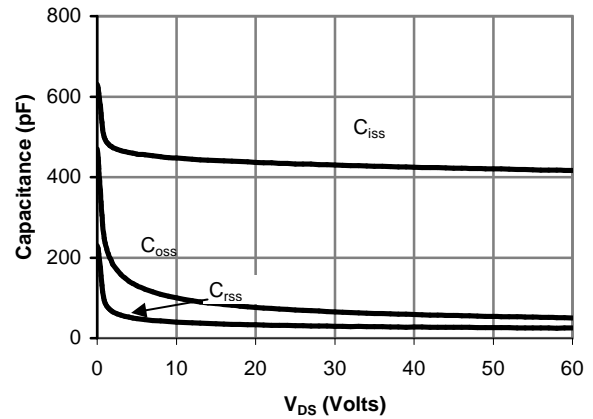


Figure 8: Capacitance Characteristics

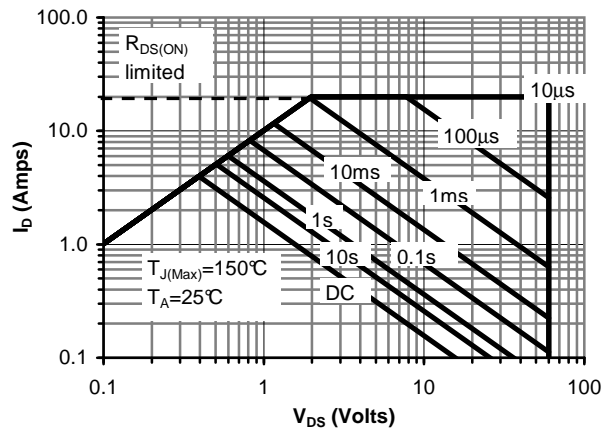


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

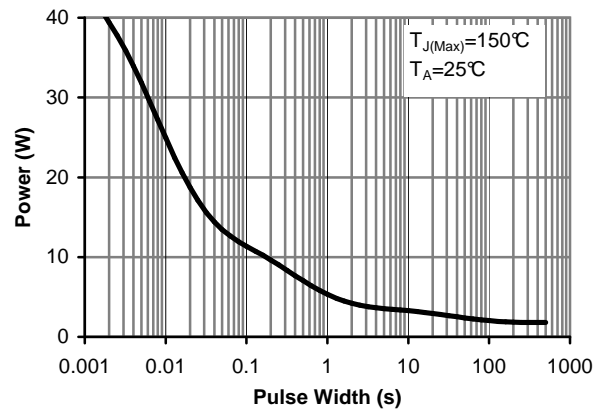


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

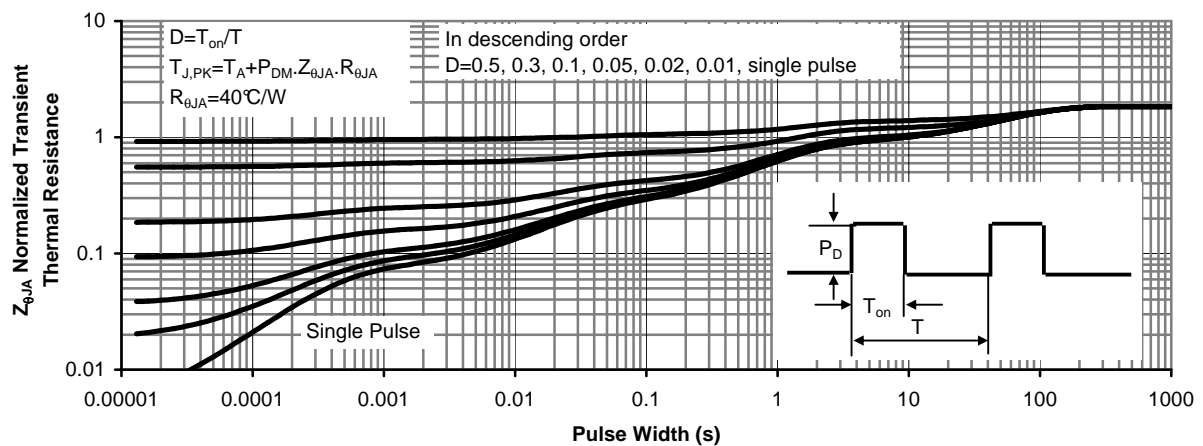


Figure 11: Normalized Maximum Transient Thermal Impedance